Preferred Device

General Purpose Transistor

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-723 package which is designed for low power surface mount applications.

• This is a Pb-Free Device

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

| Rating | Symbol | Max | Unit |
|--------------------------------|------------------|-----|------|
| Collector-Emitter Voltage | V _{CEO} | 45 | V |
| Collector-Base Voltage | V _{CBO} | 50 | V |
| Emitter-Base Voltage | V _{EBO} | 6.0 | V |
| Collector Current – Continuous | I _C | 100 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------------------------|-------------|-------------|
| Total Device Dissipation, FR-4 Board (Note 1) T _A = 25°C Derated above 25°C | P _D | 260 2.0 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient (Note 1) | R _θ JA | 480 | °C/W |
| Total Device Dissipation, FR-4 Board (Note 2) T _A = 25°C Derated above 25°C | P _D | 600 4.8 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 205 | °C/W |
| Junction and Storage Temperature Range | T _J , T _{stg} | -55 to +150 | °C |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

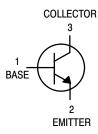
1. FR-4 @ Minimum Pad

- 2. FR-4 @ 1.0 × 1.0 Inch Pad



ON Semiconductor®

http://onsemi.com





1F = Device Code

M = Date Code

MARKING

ORDERING INFORMATION

| Device Package | | Shipping [†] | |
|----------------|---------|-----------------------|--|
| BC847BM3T5G | SOT-723 | 8000/Tape & Reel | |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|----------------------|----------|------------|-------------|----------|
| OFF CHARACTERISTICS | | | | • | I . |
| Collector – Emitter Breakdown Voltage (I _C = 10 mA) | V _{(BR)CEO} | 45 | _ | - | V |
| Collector – Emitter Breakdown Voltage $(I_C = 10 \mu A, V_{EB} = 0)$ | V _{(BR)CES} | 50 | _ | - | V |
| Collector – Base Breakdown Voltage ($I_C = 10 \mu A$) | V _{(BR)CBO} | 50 | - | - | V |
| Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$) | V _{(BR)EBO} | 6.0 | _ | - | V |
| Collector Cutoff Current $(V_{CB} = 30 \text{ V})$ $(V_{CB} = 30 \text{ V}, T_{A} = 150^{\circ}\text{C})$ | I _{CBO} | - | - - | 15 5.0 | nA μA |
| ON CHARACTERISTICS | • | | • | | • |
| DC Current Gain $ (I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V}) $ $ (I_C = 2.0 \ \text{mA}, \ V_{CE} = 5.0 \ \text{V}) $ | h _{FE} | - 200 | 150 290 | - 450 | _ |
| Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$) | V _{CE(sat)} | - | - - | 0.25 0.6 | V |
| Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA) | V _{BE(sat)} | - | 0.7 0.9 | - - | V |
| Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V) | V _{BE(on)} | 580 - | 660 - | 700 770 | mV |
| SMALL-SIGNAL CHARACTERISTICS | • | | | | |
| Current – Gain – Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 5.0$ Vdc, $f = 100$ MHz) | f _T | 100 | _ | - | MHz |
| Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz) | C _{obo} | - | _ | 4.5 | pF |
| Noise Figure (I _C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz) | NF | _ | _ | 10 | dB |

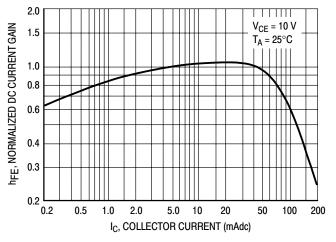


Figure 1. Normalized DC Current Gain

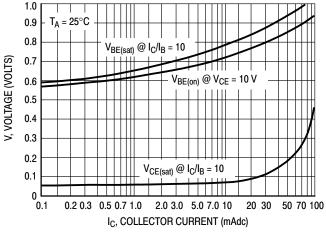


Figure 2. "Saturation" and "On" Voltages

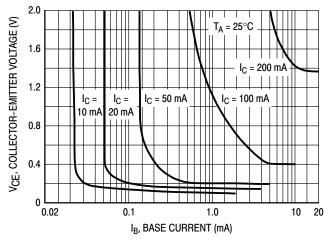


Figure 3. Collector Saturation Region

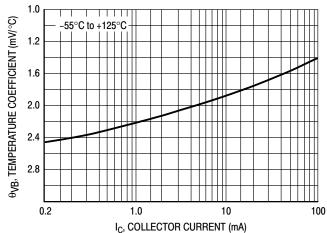
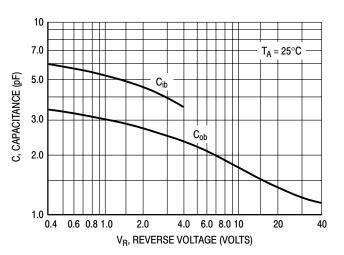


Figure 4. Base-Emitter Temperature Coefficient

BC847



 f_{T} , CURRENT-GAIN – BANDWIDTH PRODUCT (MHz) 400 300 200 V_{CE} = 10 V T_A = 25°C 100 80 60 40 30 20 0.5 0.7 1.0 2.0 3.0 5.0 7.0 10 20 30 50 I_C, COLLECTOR CURRENT (mAdc)

Figure 5. Capacitances

Figure 6. Current-Gain - Bandwidth Product



SOT-723 CASE 631AA-01 ISSUE D

DATE 10 AUG 2009

NOTES:

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

| | MILLIMETERS | | | |
|-----|-------------|------|------|--|
| DIM | MIN | NOM | MAX | |
| Α | 0.45 | 0.50 | 0.55 | |
| b | 0.15 | 0.21 | 0.27 | |
| b1 | 0.25 | 0.31 | 0.37 | |
| С | 0.07 | 0.12 | 0.17 | |
| D | 1.15 | 1.20 | 1.25 | |
| E | 0.75 | 0.80 | 0.85 | |
| е | 0.40 BSC | | | |
| ΗE | 1.15 | 1.20 | 1.25 | |
| L | 0.29 REF | | | |
| 12 | 0.15 | 0.20 | 0.25 | |

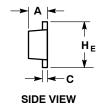
L2 0.15 0.20 0.25 **GENERIC** MARKING DIAGRAM*

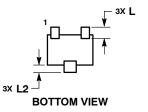


= Specific Device Code XX Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

-X-2X b ⊕ 0.08 X Y **TOP VIEW**

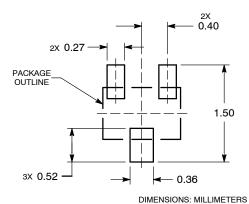




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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|------------------|-------------|--|-------------|
| DESCRIPTION: | SOT-723 | | PAGE 1 OF 1 |

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